

ABSTRACT OF THE DISCLOSURE

The present method prevents malfunctions in switching caused by a light leakage current in an active matrix type thin film transistor substrate for a liquid crystal display and prevents display failures, by selectively disposing a self assembled monolayer film in a gate electrode-projected region of the surface of an insulator film with high definition, and by selectively improving the orientation order of an organic semiconductor film only in the gate electrode-projected region without improving the order at an irradiated portion with light outside the gate electrode-projected region.